

MOS FIELD EFFECT TRANSISTOR

3SK230

RF AMP. FOR VHF/CATV TUNER N-CHANNEL SILICON DUAL-GATE MOS FIELD-EFFECT TRANSISTOR 4 PINS MINI MOLD

FEATURES

• The Characteristic of Cross-Modulation is good. CM = 108 dB μ (TYP.) @f = 470 MHz, GR = -30 dB

Low Noise Figure NF1 = 2.2 dB TYP. (@ = 470 MHz)

NF2 = 0.9 dB TYP. (@ = 55 MHz)

High Power Gain GPS = 19.5 dB TYP. (@ = 470 MHz)

· Enhancement Typ.

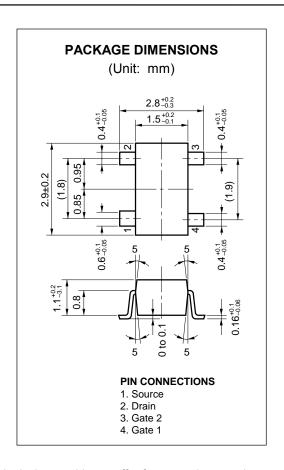
· Suitable for use as RF amplifier in CATV tuner.

· Automatically Mounting: Embossed Type Taping

· Small Package: 4 Pins Mini Mold Package. (SC-61)

ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

Drain to Source Voltage	VDSX	18	V
Gate1 to Source Voltage	V _{G1S}	±8(±10)*1	V
Gate2 to Source Voltage	V _{G2} S	±8(±10)* ¹	V
Gate1 to Drain Voltage	V_{G1D}	18	V
Gate2 to Drain Voltage	V_{G2D}	18	V
Drain Current	lo	25	mΑ
Total Power Dissipation	PD	200	mW
Channel Temperature	Tch	125	°C
Storage Temperature	Tstg	-55 to +125	°C
$R_L \ge 10 \text{ k}\Omega$			



PRECAUTION: Avoid high static voltages or electric fields so that this device would not suffer from any damage due to those voltages or fields.

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ELECTRICAL CHARACTERISTICS (TA = 25 °C)

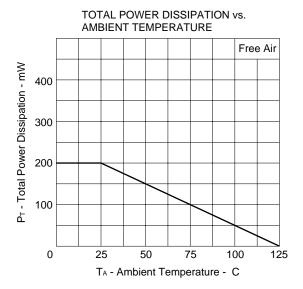
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Drain to Source Breakdown Voltage	BVDSX	18			V	$V_{G1S} = V_{G2S} = -2 \text{ V}, I_D = 10 \mu\text{A}$	
Drain Current	IDSX	0.01		8.0	mA	V _{DS} = 6 V, V _{G2S} = 4.5 V, V _{G1S} = 0.75 V	
Gate1 to Source Cutoff Voltage	V _{G1S(off)}	0		+1.0	V	$V_{DS} = 6 \text{ V}, V_{G2S} = 3 \text{ V}, I_{D} = 10 \mu\text{A}$	
Gate2 to Source Cutoff Voltage	V _{G2S(off)}	+0.6	+1.1	+1.6	٧	$V_{DS} = 6 \text{ V}, V_{G1S} = 3 \text{ V}, I_{D} = 10 \mu\text{A}$	
Gate1 Reverse Current	I _{G1SS}			±20	nA	V _{DS} = V _{G2S} = 0, V _{G1S} = ±8 V	
Gate2 Reverse Current	I _{G2SS}			±20	nA	V _{DS} = V _{G1S} = 0, V _{G2S} = ±8 V	
Forward Transfer Admittance	y fs	16	20	24	mS	V _{DS} = 6 V, V _{G2S} = 4.5 V, I _D = 10 mA f = 1 kHz	
Input Capacitance	Ciss	2.3	2.8	3.3	pF	V _{DS} = 6 V, V _{G2S} = 4.5 V, I _D = 10 mA f = 1 MHz	
Output Capacitance	Coss	0.9	1.2	1.5	pF		
Reverse Transfer Capacitance	Crss		0.015	0.03	pF		
Power Gain	Gps	16.5	19.5	22.5	dB	V _{DS} = 6 V, V _{G2S} = 4.5 V, I _D = 10 mA f = 470 MHz	
Noise Figure 1	NF1		2.2	3.2	dB		
Noise Figure 2	NF2		0.9	2.4	dB	V _{DS} = 6 V, V _{G2S} = 4.5 V, I _D = 10 mA f = 55 MHz	

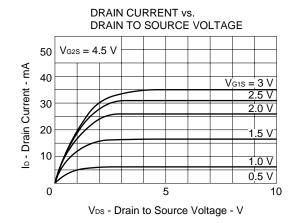
★ IDSX Classification

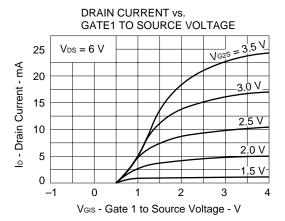
Rank	U1A/UAA *	U1B/UAB *		
Marking	U1A	U1B		
I _{DSX} (mA)	0.01 to 3.0	1.0 to 8.0		

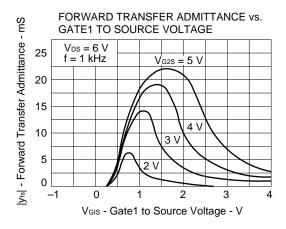
^{*} Old Specification / New Specification

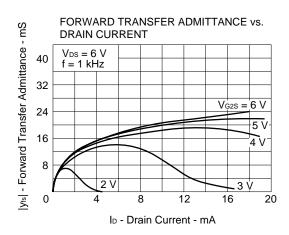
CHARACTERISTIC CURVE (TA = 25 °C)

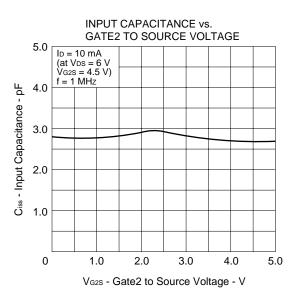


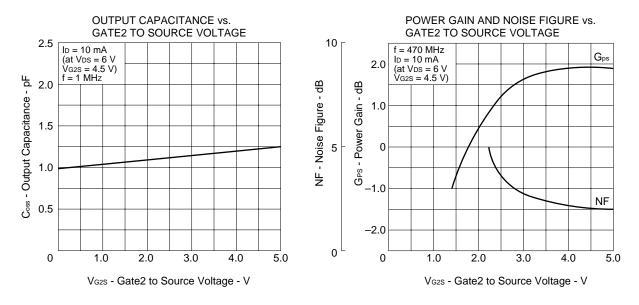










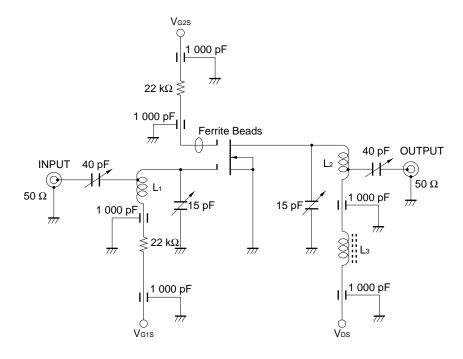


S-PARAMETER

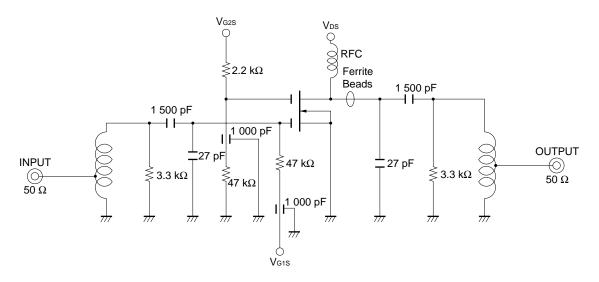
 V_{DS} = 6 V, V_{G2S} = 4.5 V, I_D = 10 mA, (Z_O = 50 Ω)

FREQUENC Y	S11		Sź	S21		S12		S22	
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG	
100	1.000	-14.7	2.160	160.5	0.008	12.8	0.942	-8.2	
200	0.960	-24.5	1.953	148.3	0.003	81.1	0.947	-9.6	
300	0.926	-34.3	1.868	135.8	0.005	-146.8	0.906	-16.4	
400	0.876	-45.0	1.760	121.2	0.003	-59.5	0.908	-19.4	
500	0.853	-54.4	1.691	109.4	0.003	84.3	0.915	-25.1	
600	0.842	-63.1	1.608	97.6	0.004	-87.0	0.889	-29.0	

GPS AND NF TEST CIRCUIT AT f = 470 MHz



NF TEST CIRCUIT AT f = 55 MHz



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▶Business issue

NEC Compound Semiconductor Devices, Ltd.

5th Sales Group, Sales Division TEL: +81-3-3798-6372 FAX: +81-3-3798-6783 E-mail: salesinfo@csd-nec.com

NEC Compound Semiconductor Devices Hong Kong Limited

Hong Kong Head Office TEL: +852-3107-7303 FAX: +852-3107-7309
Taipei Branch Office TEL: +886-2-8712-0478 FAX: +886-2-2545-3859
Korea Branch Office TEL: +82-2-528-0301 FAX: +82-2-528-0302

NEC Electron Devices European Operations http://www.nec.de/

TEL: +49-211-6503-101 FAX: +49-211-6503-487

California Eastern Laboratories, Inc. http://www.cel.com/

TEL: +1-408-988-3500 FAX: +1-408-988-0279

▶ Technical issue

NEC Compound Semiconductor Devices, Ltd. http://www.csd-nec.com/

Sales Engineering Group, Sales Division

E-mail: techinfo@csd-nec.com FAX: +81-44-435-1918